

1N5400-G Thru. 1N5408-G

Voltage: 50 to 1000 V

Current: 3.0 A

RoHS Device

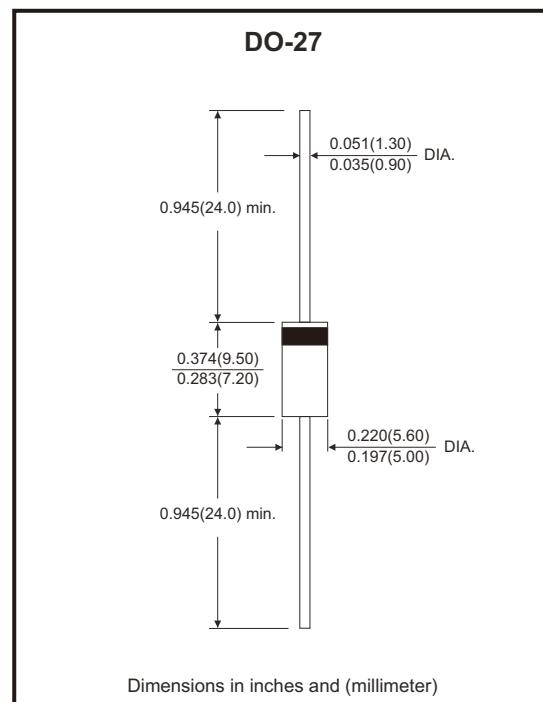


Features

- Open junction chip.
- Low reverse leakage.
- High forward surge current capability.
- High temperature soldering guaranteed 250°C/10 seconds at terminals.

Mechanical data

- Epoxy: UL 94V-0 rate flame retardant.
- Case: DO-27, molded plastic.
- Terminals: Solder plated, solderable per MIL-STD-750, method 2026.
- Polarity: Color band denotes cathode.
- Mounting position: Any.



Circuit Diagram



Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Parameter	Symbol	1N5400 -G	1N5401 -G	1N5402 -G	1N5404 -G	1N5406 -G	1N5407 -G	1N5408 -G	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward rectified current at $T_L=100^\circ\text{C}$	$I_{F(AV)}$					3.0			A
Peak forward surge current, 8.3ms single half sine-wave superimposed on rated load	I_{FSM}					150			A
Maximum instantaneous forward voltage at 3.0A	V_F				1.10				V
Maximum DC reverse current @ $T_A=25^\circ\text{C}$ @ $T_A=125^\circ\text{C}$	I_R				10.0				μA
Typical junction capacitance (Note 1)	C_J				50				pF
Typical thermal resistance	$R_{\theta JA}$				45				$^\circ\text{C/W}$
Operating junction and storage temperature range	T_J, T_{STG}				-55 to +150				$^\circ\text{C}$

Notes: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

Company reserves the right to improve product design , functions and reliability without notice.

REV:C

General Purpose Silicon Rectifiers

Comchip
SMD Diode Specialist

Rating and Characteristic Curves (1N5400-G Thru. 1N5408-G)

Fig.1 - Derating Curve Output Rectified Current

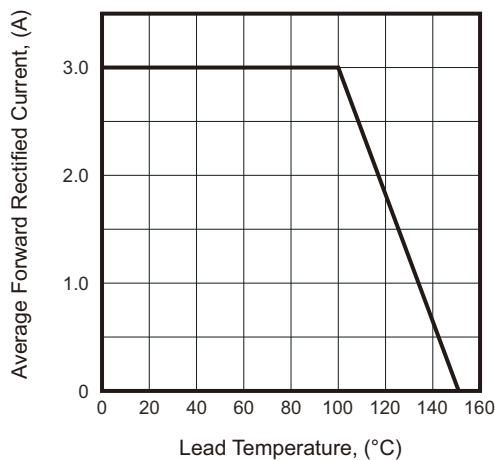


Fig.2 - Max. Non-Repetitive Peak Forward Surge Current Per Leg

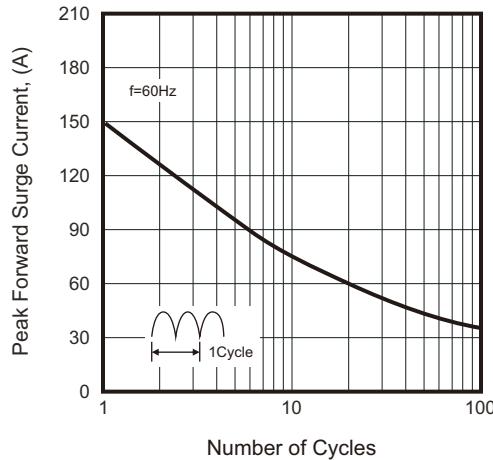


Fig.3 - Typical Forward Voltage Characteristics

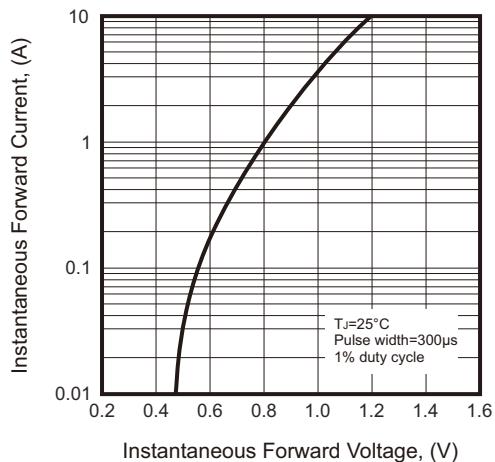
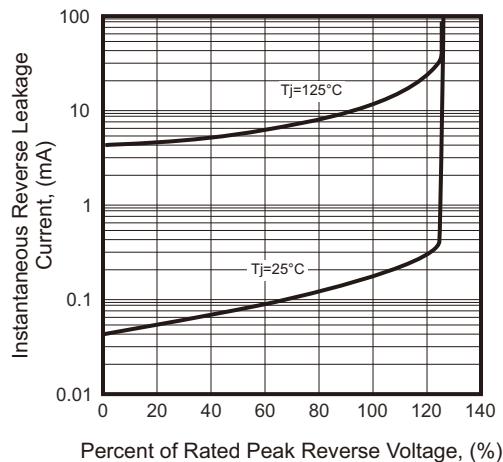
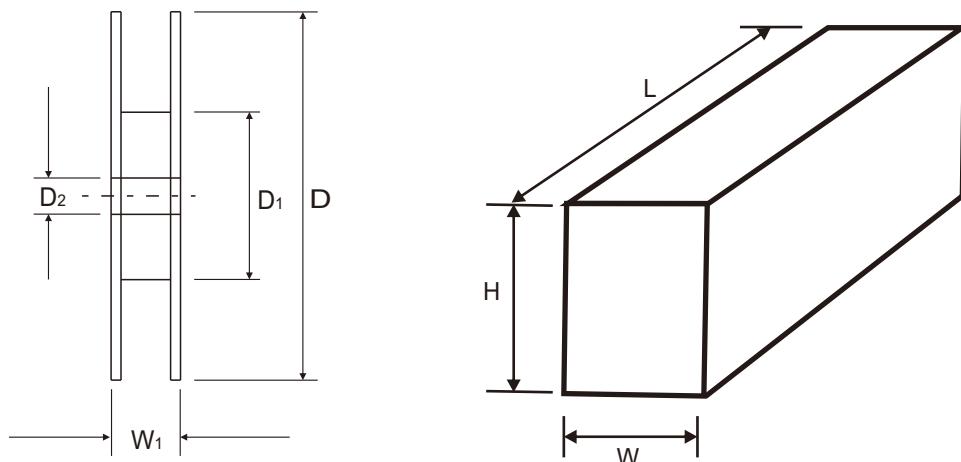
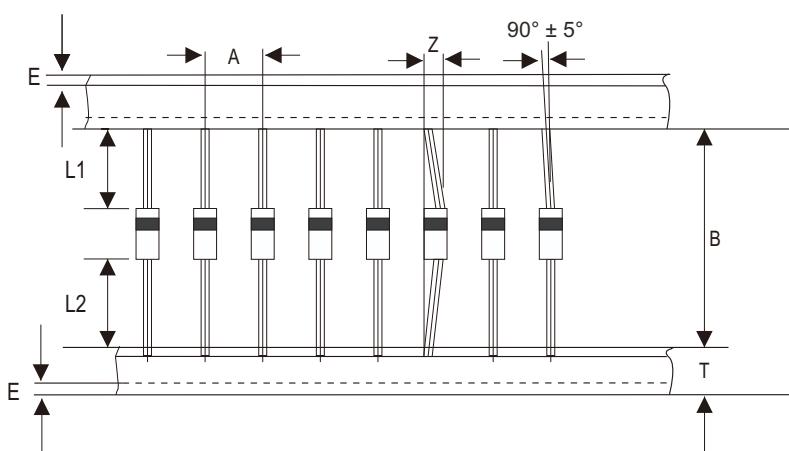


Fig.4 - Typical Reverse Leakage Characteristics



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Taping Specification For Axial Lead Diodes



DO-27	SYMBOL	A	B	Z	T	E	$ L_1-L_2 $
	(mm)	10.00 ± 0.50	52.40 ± 1.50 -0.40	1.20 (max)	6.00 ± 0.40	0.80 (max)	1.00 (max)
	(inch)	0.394 ± 0.020	2.063 ± 0.059 -0.016	0.047 (max)	0.236 ± 0.016	0.031 (max)	0.039 (max)

DO-27	SYMBOL	L	W	H	D	D1	D2	W1
	(mm)	255.00 ± 5.00	75.00 ± 5.00	150.00 ± 5.00	330	85.70 ± 0.30	16.60 ± 0.40	79.00 ± 1.00
	(inch)	10.039 ± 0.197	2.953 ± 0.197	5.906 ± 0.197	12.992	3.374 ± 0.012	0.654 ± 0.016	3.110 ± 0.039

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REV:C